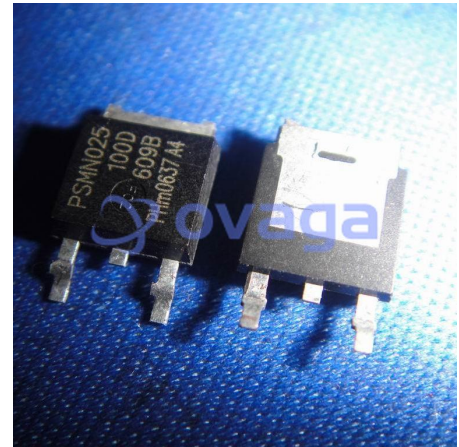


N-channel TrenchMOS transistor (N-channel TrenchMOS transistor)

Manufacturers	NXP Semiconductor
Package/Case	TO-252
Product Type	Discrete Semiconductors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for PSMN025-100D or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

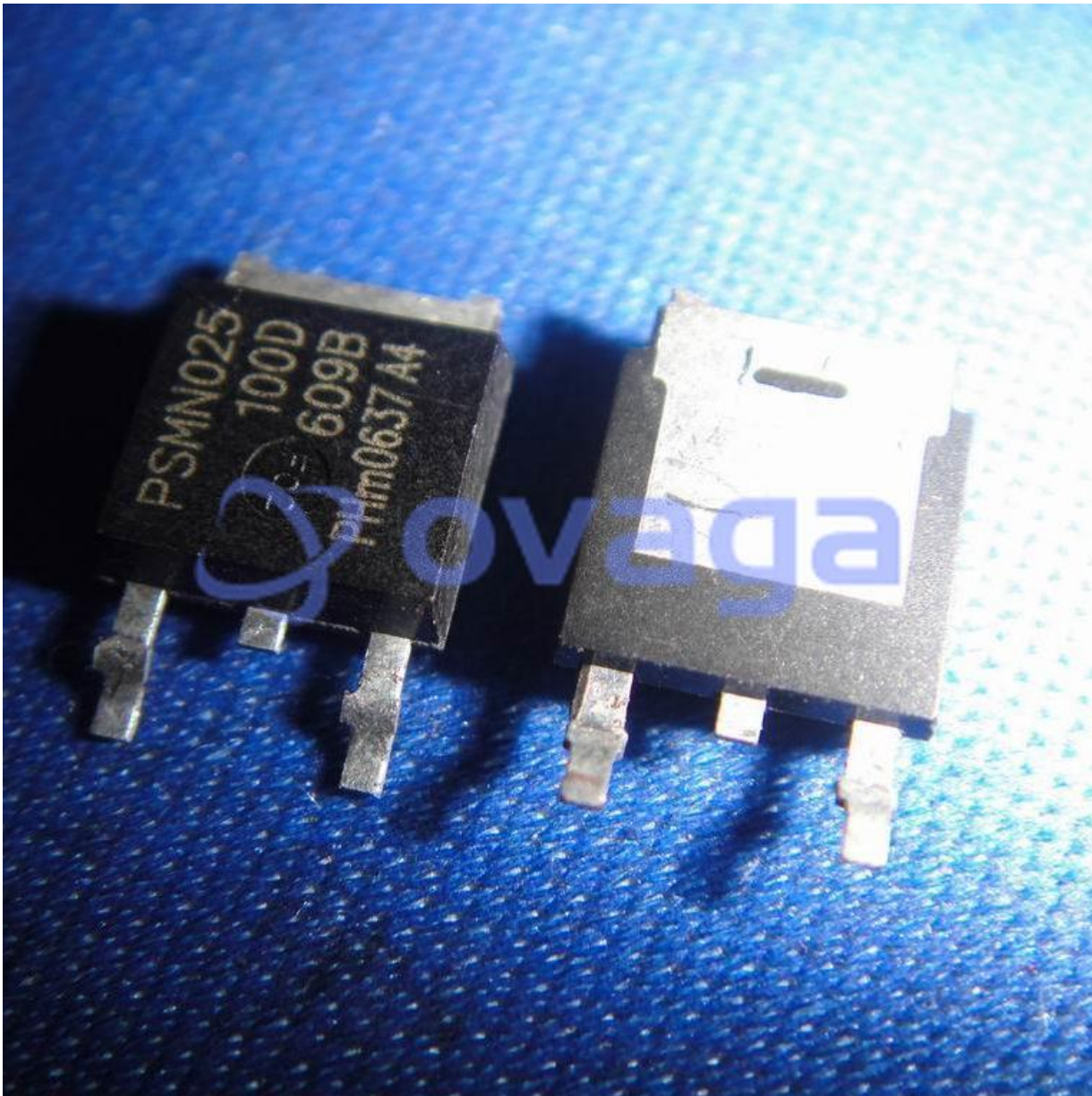
PSMN025-100D is a specific type of MOSFET (metal-oxide-semiconductor field-effect transistor) that is designed for use in high-performance applications that require a low on-resistance and fast switching speeds. It is manufactured by NXP Semiconductors and is part of their TrenchMOS technology platform.

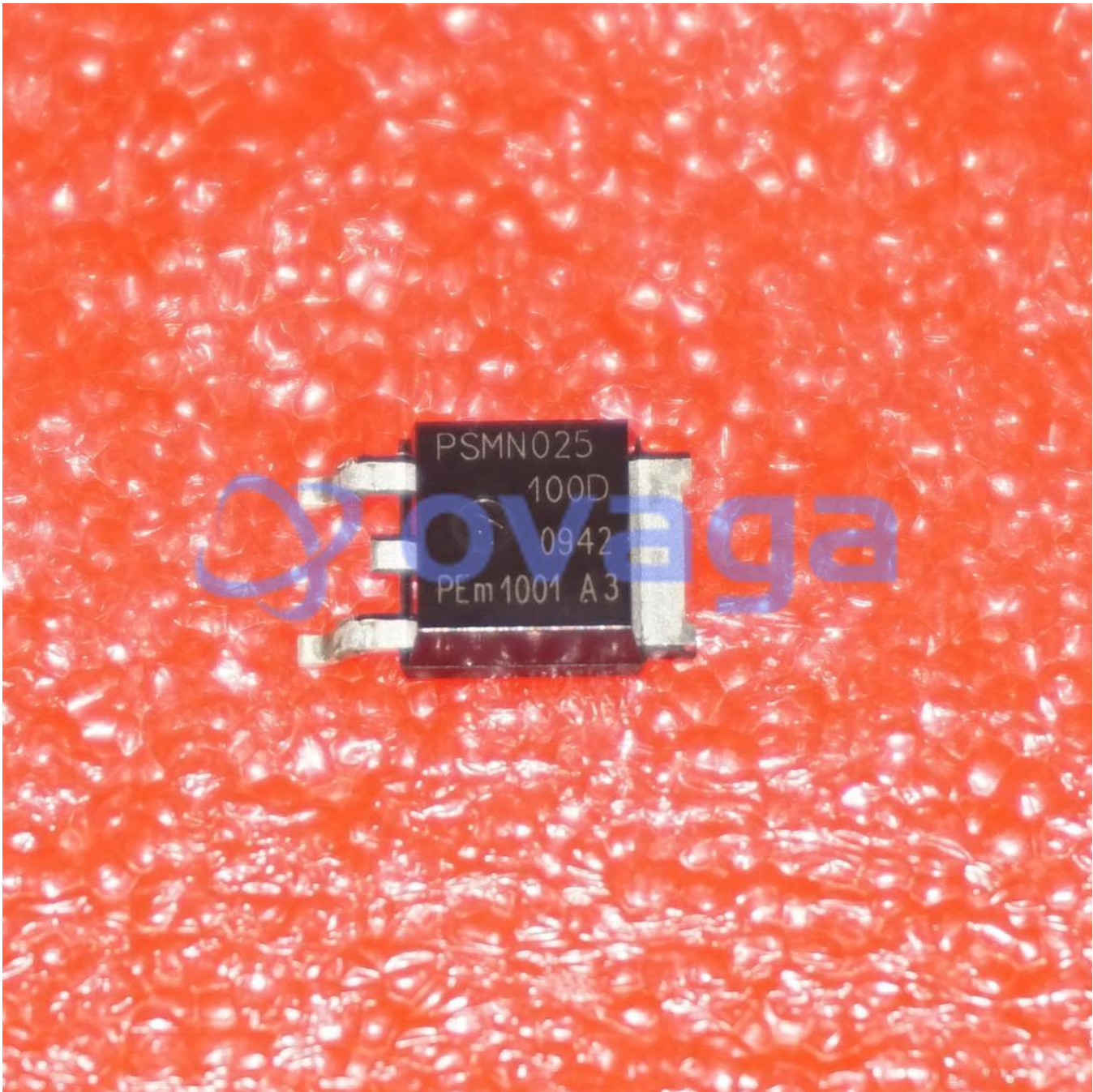
Features

- Drain-source voltage rating of 100V
- Continuous drain current rating of 110A
- Low on-resistance of 2.5mOhm
- Fast switching speeds
- TO-220AB package

Application

- IRFS7430-7P
- FDS4435BZ
- STPSC2006CW
- NTMF55C604NLT1G
- AUIRF7739L2TR
- IPP65R125CPXKSA1





Related Products



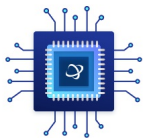
[PSMN063-150D](#)

NXP Semiconductor
TO-252



[PSMN5R0-30YL](#)

NXP Semiconductor
SOT-669



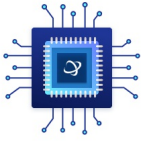
[PSMN4R0-60YS](#)

NXP Semiconductor



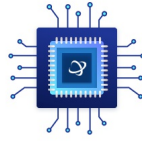
[PSMN5R5-60YS](#)

NXP Semiconductor



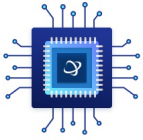
[PSMN011-60MSX](#)

NXP Semiconductor



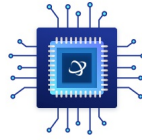
[PSMN011-60MS](#)

NXP Semiconductor



[PSMN4R0-30YLDX](#)

NXP Semiconductor



[PSMN1R4-40YLD](#)

NXP Semiconductor